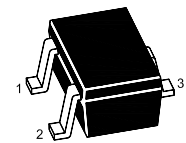


MMDT5113W-AH

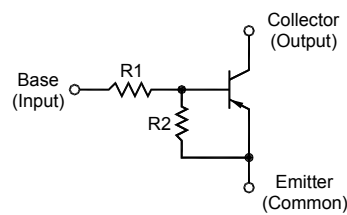
PNP Silicon Epitaxial Planar Digital Transistor

Features

- AEC-Q101 Qualified and PPAP Capable
- Halogen and Antimony Free(HAF), RoHS compliant



1.Base 2.Emitter 3.Collector
SOT-323 Plastic Package

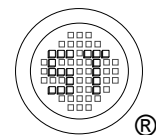


Resistance Values

R1 (K Ω)	R2 (K Ω)
47	47

Absolute Maximum Ratings (T_a = 25°C)

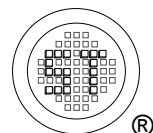
Parameter	Symbol	Value	Unit
Collector Base Voltage	-V _{CBO}	50	V
Collector Emitter Voltage	-V _{CEO}	50	V
Collector Current	-I _C	100	mA
Total Power Dissipation	P _{tot}	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C

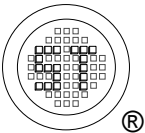
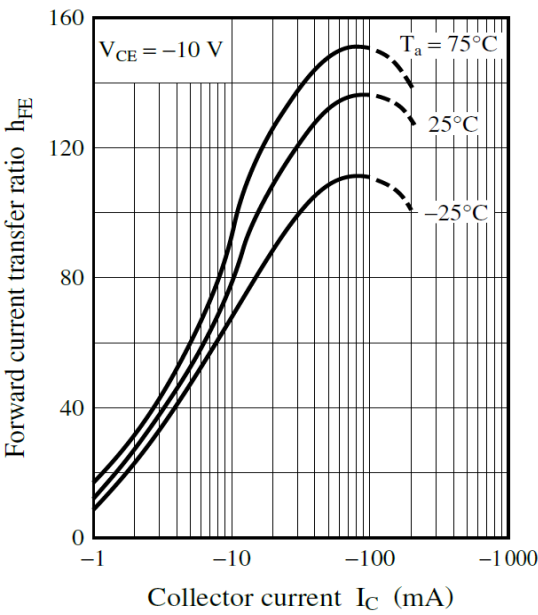
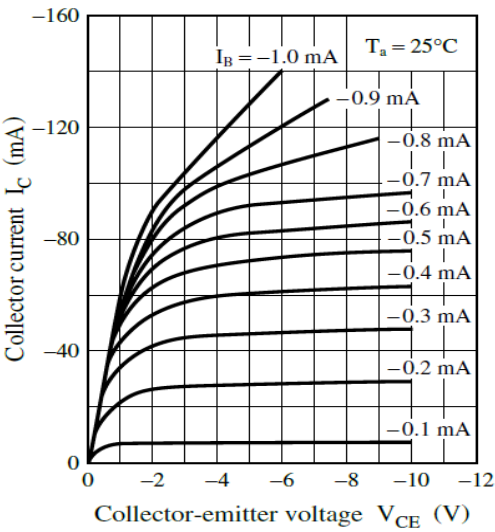
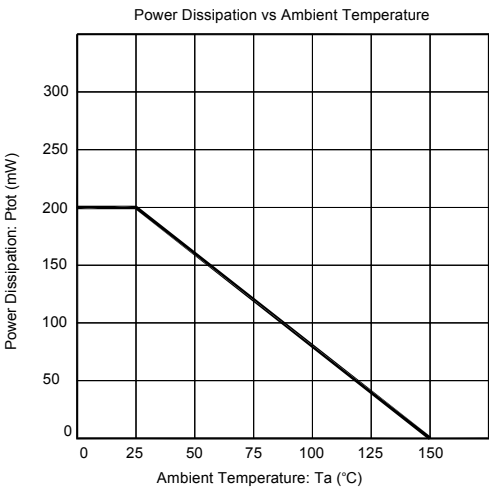


MMDT5113W-AH

Characteristics at $T_a = 25^\circ\text{C}$

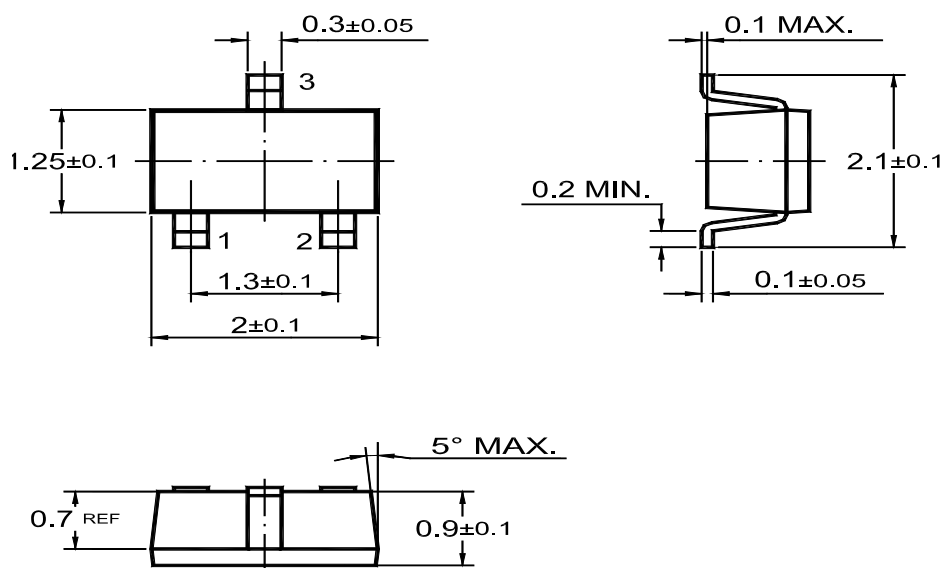
Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$	h_{FE}	80	-	-	-
Collector Base Cutoff Current at $-V_{CB} = 50\text{ V}$	$-I_{CBO}$	-	-	100	nA
Emitter Base Cutoff Current at $-V_{EB} = 6\text{ V}$	$-I_{EBO}$	-	-	0.1	mA
Collector Base Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	50	-	-	V
Collector Emitter Breakdown Voltage at $-I_C = 2\text{ mA}$	$-V_{(BR)CEO}$	50	-	-	V
Collector Emitter Saturation Voltage at $-I_C = 10\text{ mA}$, $-I_B = 0.5\text{ mA}$	$-V_{CEsat}$	-	-	0.3	V
Input Voltage (ON) at $-V_O = 0.3\text{ V}$, $-I_O = 10\text{ mA}$	$-V_{I(ON)}$	-	-	3	V
Input Voltage (OFF) at $-V_{CC} = 5\text{ V}$, $-I_O = 100\text{ }\mu\text{A}$	$-V_{I(OFF)}$	0.5	-	-	V
Transition Frequency at $-V_{CB} = 10\text{ V}$, $-I_E = 5\text{ mA}$, $f = 100\text{ MHz}$	f_T	-	250	-	MHz



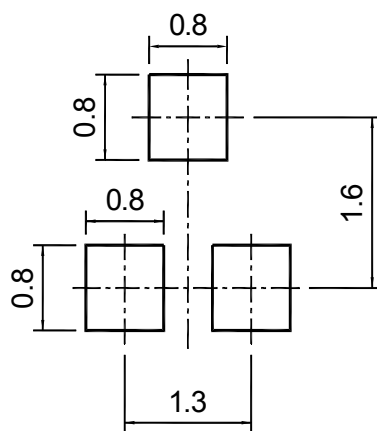


PACKAGE OUTLINE

(Dimensions in mm)



Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-323	8	4 ± 0.1	0.157 ± 0.004	330	13	10,000

